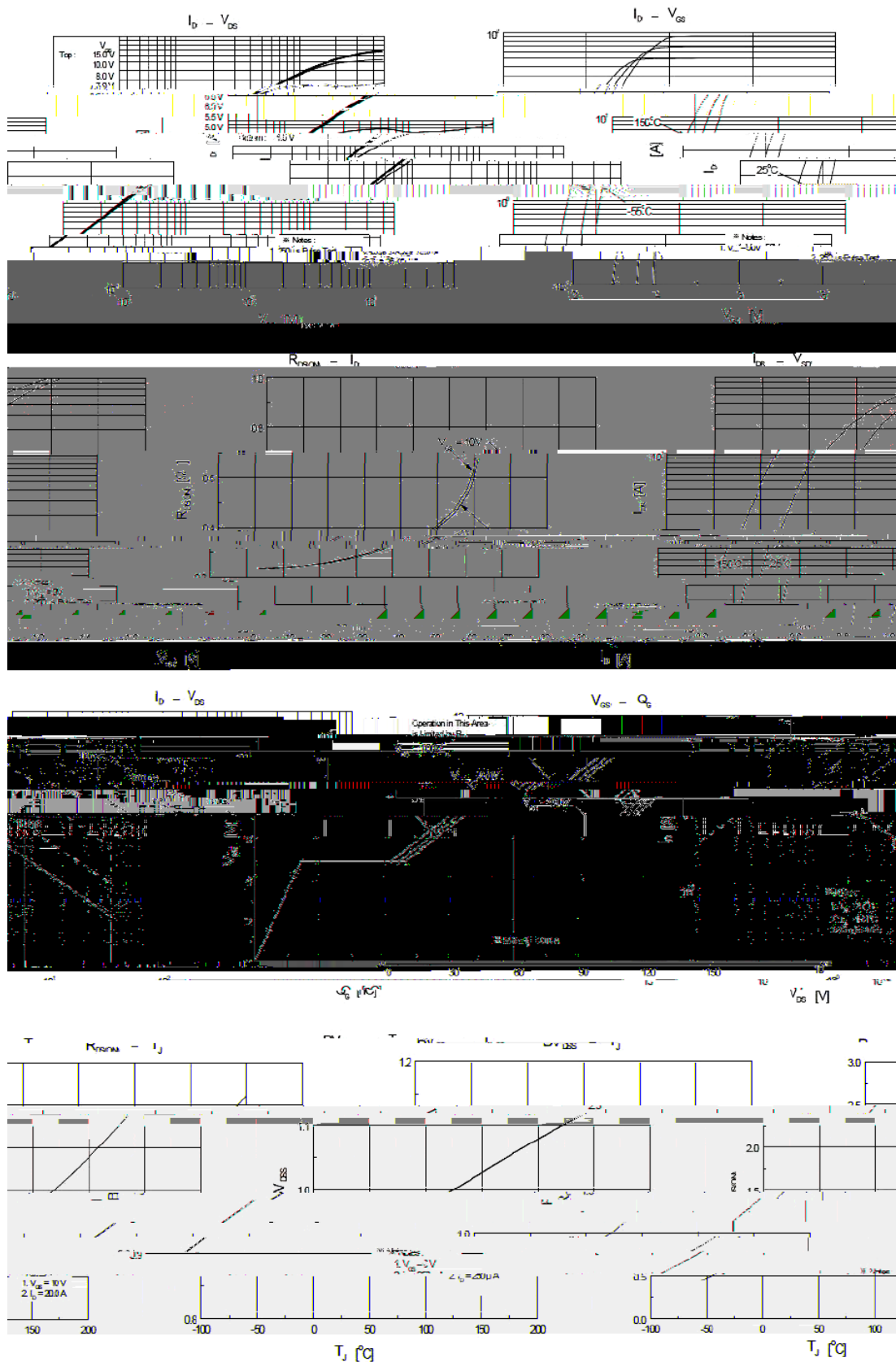
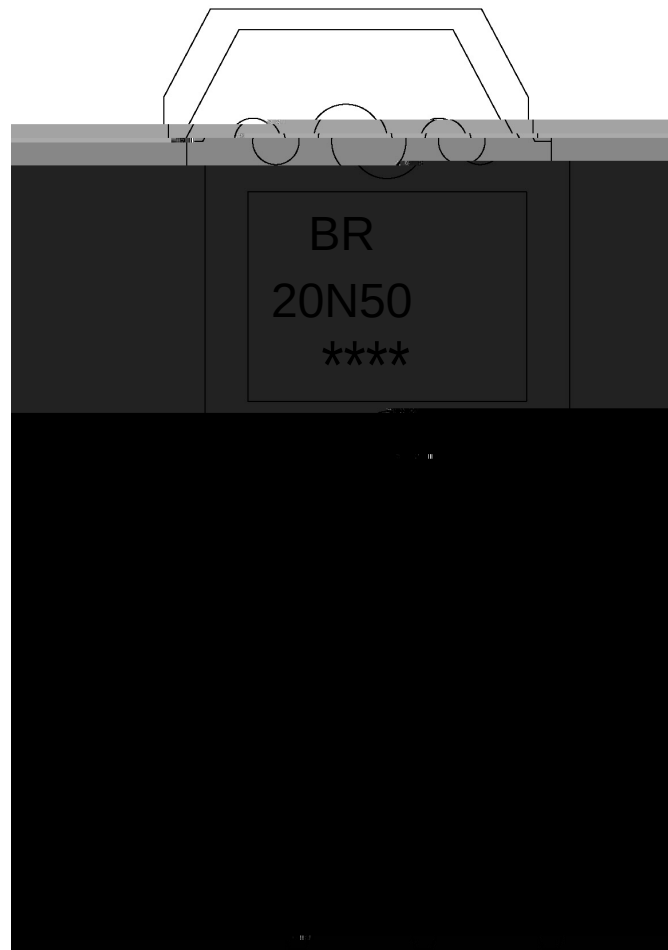


Parameter	Symbol	Rating	Unit
Drain-to-Source Breakdown Voltage	V_{DSS}	500	V
Continuous Drain Current	$I_D(T_c=25^\circ\text{C})$	20	A
Continuous Drain Current	$I_D(T_c=100^\circ\text{C})$	13	A
Drain Current Pulsed	I_{DP}	80	A
Gate-to-Source Voltage	V_{GSS}	± 30	V
Repetitive Avalanche Energy	E_{AR}	28	mJ
Single Pulse Avalanche Energy	E_{AS}	1110	mJ
Peak Diode Recovery dv/dt	dv/dt	4.5	V/ns
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	280	W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	





BR:

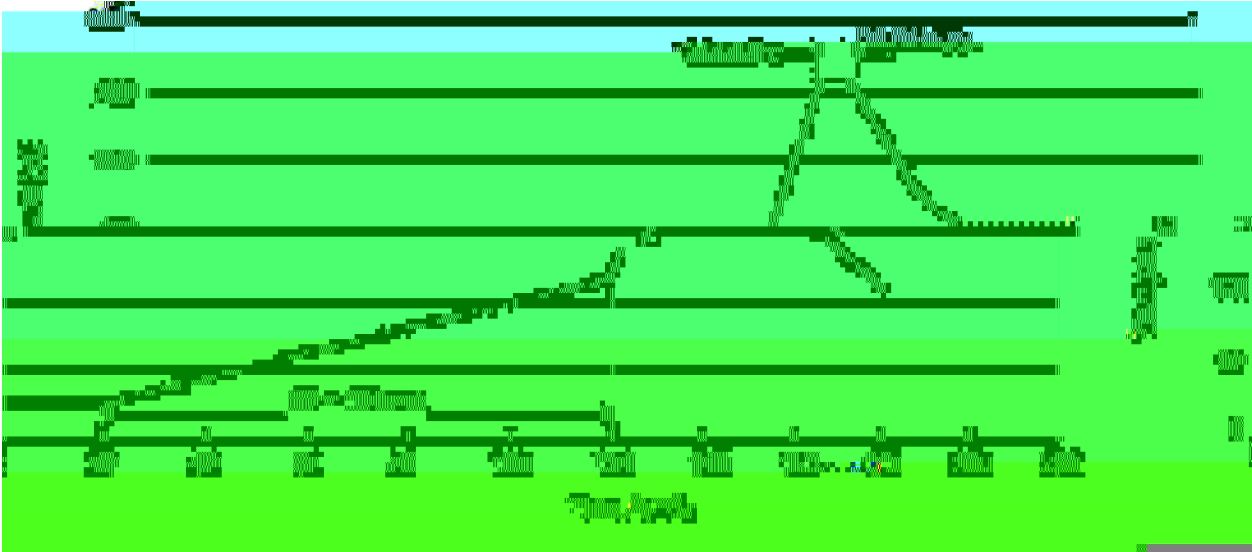
20N50

Note:

BR: Company Code.

20N50: Product Type.

****: Lot No. Code, code change with Lot No.



Note:

- | | | | |
|---|--------|-----------|--|
| 1 | 25 150 | 60 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 2534.98(2.Peak35340;)T53.7.00174 222: TD7(:)-3.1(25~1504ETj |